

L Number	Hits	Search Text	DB	Time stamp
1	5	integrated same device same heat\$3 same microfluid	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:38
2	14978	integrated same device same heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:39
3	756	(integrated same device same heat\$3) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:41
4	688	((integrated same device same heat\$3) and mosfet) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:41
5	618	((((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:42
6	0	(((((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor) and heated adj chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:47
7	14	(((((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor) and chamber near2 adjacent	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:44
8	139	(((((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor) and chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:48
9	0	(((((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor) and chamber) and 392/407	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:49
10	0	(((((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor) and chamber) and 219/4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:48

11	1	(((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor) and chamber) and 219/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:49
13	0	(((integrated same device same heat\$3) and mosfet) and semiconductor) and 392/407	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:52
12	5	(((integrated same device same heat\$3) and mosfet) and semiconductor) and 219/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:53
14	0	((integrated same device same heat\$3) and mosfet) and 392/407	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:52
15	6	(integrated same device same heat\$3) and 392/407	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:52
16	9	((integrated same device same heat\$3) and mosfet) and 219/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:56
17	176	(((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor) and source adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:57
18	169	(((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor) and source adj region) and drain adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:57
19	94	(((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor) and source adj region) and drain adj region) and channel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:58
20	10	(((integrated same device same heat\$3) and mosfet) and semiconductor) and transistor) and source adj region) and drain adj region) and channel adj region) and dielectric adj layer same gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 11:06

21	46	4035607, 4506272, "5693545"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 11:07
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L Number	Hits	Search Text	DB	Time stamp
1	5	heater same microchip same micro\$fluid\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:38
3	0	(heater same microchip same micro\$fluid\$3) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:38
2	1	(heater same microchip same micro\$fluid\$3) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:39
4	3	(heater same microchip same micro\$fluid\$3) and fluid adj chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:43
5	0	((heater same microchip same micro\$fluid\$3) and transistor) and ((heater same microchip same micro\$fluid\$3) and fluid adj chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:39
6	1	((heater same microchip same micro\$fluid\$3) and semiconductor) and ((heater same microchip same micro\$fluid\$3) and fluid adj chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:39
7	0	inegrated adj2 heater	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:42
8	517	integrated adj2 heater	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:43
9	133	(integrated adj2 heater) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:43
11	0	((((integrated adj2 heater) and semiconductor) and transistor) and fluid adj chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:55

12	0	((integrated adj2 heater) and semiconductor) and fluid adj chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:45
13	8	(integrated adj2 heater) and fluid adj chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:46
14	22	((integrated adj2 heater) and semiconductor) and transistor) and chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 09:13
15	0	((integrated adj2 heater) and semiconductor) and transistor) and liquid adj chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 08:55
16	0	((integrated adj2 heater) and semiconductor) and transistor) and heated adj object	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 09:14
17	9	((integrated adj2 heater) and semiconductor) and transistor) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 09:15
18	5	((integrated adj2 heater) and semiconductor) and transistor) and mosfet) and source adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 09:15
19	5	((integrated adj2 heater) and semiconductor) and transistor) and mosfet) and source adj region) and drain adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 09:15
21	4	((integrated adj2 heater) and semiconductor) and transistor) and mosfet) and source adj region) and drain adj region) and channel adj region) and dielectric adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 09:16
22	4	((integrated adj2 heater) and semiconductor) and transistor) and mosfet) and source adj region) and drain adj region) and channel adj region) and dielectric adj layer) and gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 09:16

20	5	((((integrated adj2 heater) and semiconductor) and transistor) and mosfet) and source adj region) and drain adj region) and channel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 09:18
10	59	((integrated adj2 heater) and semiconductor) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 09:19